PDTC123Y series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω Rev. 04 — 16 November 2009 Product data sh

Product data sheet

Product profile

1.1 General description

NPN Resistor-Equipped Transistors (RET) family.

Table 1. **Product overview**

Type number	Package		PNP complement	
	NXP	JEITA	JEDEC	
PDTC123YE	SOT416	SC-75	-	PDTA123YE
PDTC123YK	SOT346	SC-59A	TO-236	PDTA123YK
PDTC123YM	SOT883	SC-101	-	PDTA123YM
PDTC123YS[1]	SOT54	SC-43A	TO-92	PDTA123YS
PDTC123YT	SOT23	-	TO-236AB	PDTA123YT
PDTC123YU	SOT323	SC-70	-	PDTA123YU

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

Circuit drivers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	



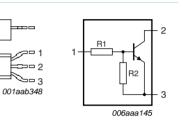
2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline Symbol
SOT54		
1	input (base)	
2	output (collector)	2
3	GND (emitter)	001aab347 R1 R2

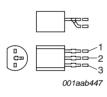
SC)T 5	4A

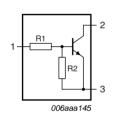
1	input (base)
2	output (collector)
3	GND (emitter)



SOT54 variant

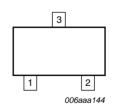
1	input (base)
2	output (collector)
3	GND (emitter)

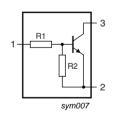




SOT23; SOT323; SOT346; SOT416

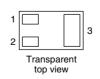
1	input (base)
2	GND (emitter)
3	output (collector)

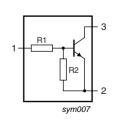




SOT883

1	input (base)
2	GND (emitter)
3	output (collector)





3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTC123YE	SC-75	plastic surface mounted package; 3 leads	SOT416			
PDTC123YK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTC123YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTC123YS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTC123YT	-	plastic surface mounted package; 3 leads	SOT23			
PDTC123YU	SC-70	plastic surface mounted package; 3 leads	SOT323			

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

in i	
Type number	Marking code ^[1]
PDTC123YE	19
PDTC123YK	31
PDTC123YM	G7
PDTC123YS	TC123Y
PDTC123YT	*AL
PDTC123YU	*19

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	N	lin	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-		50	V
V_{CEO}	collector-emitter voltage	open base	-		50	V
V_{EBO}	emitter-base voltage	open collector	-		5	V
V_{I}	input voltage					
	positive		-		+12	V
	negative		-		-5	V
Io	output current (DC)		-		100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1$ ms	-		100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$				
	SOT416		<u>[1]</u> _		150	mW
	SOT346		<u>[1]</u> _		250	mW
	SOT883		[2][3]		250	mW
	SOT54		[1] _		500	mW
	SOT23		<u>[1]</u> _		250	mW
	SOT323		[1] _		200	mW
T _{stg}	storage temperature		-	65	+150	°C
Tj	junction temperature		-		150	°C
T _{amb}	ambient temperature		-	65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT346		<u>[1]</u> -	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> -	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> -	-	625	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

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NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

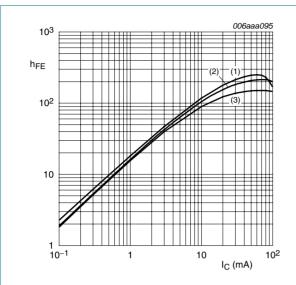
Characteristics 7.

Product data sheet

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	700	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	35	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.75	0.3	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 300 \text{ mV}; I_{C} = 20 \text{ mA}$	2.5	1.15	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	$k\Omega$
R2/R1	bias resistor ratio		3.6	4.5	5.5	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2	pF
-						

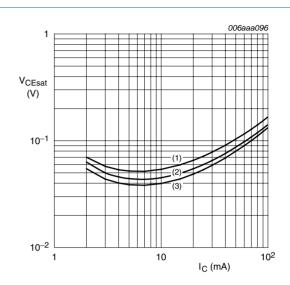


$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



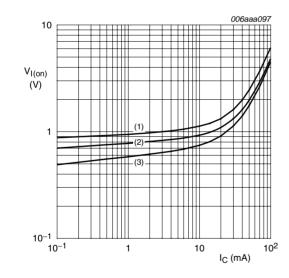
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



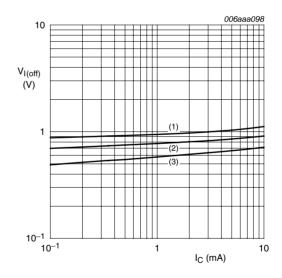
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

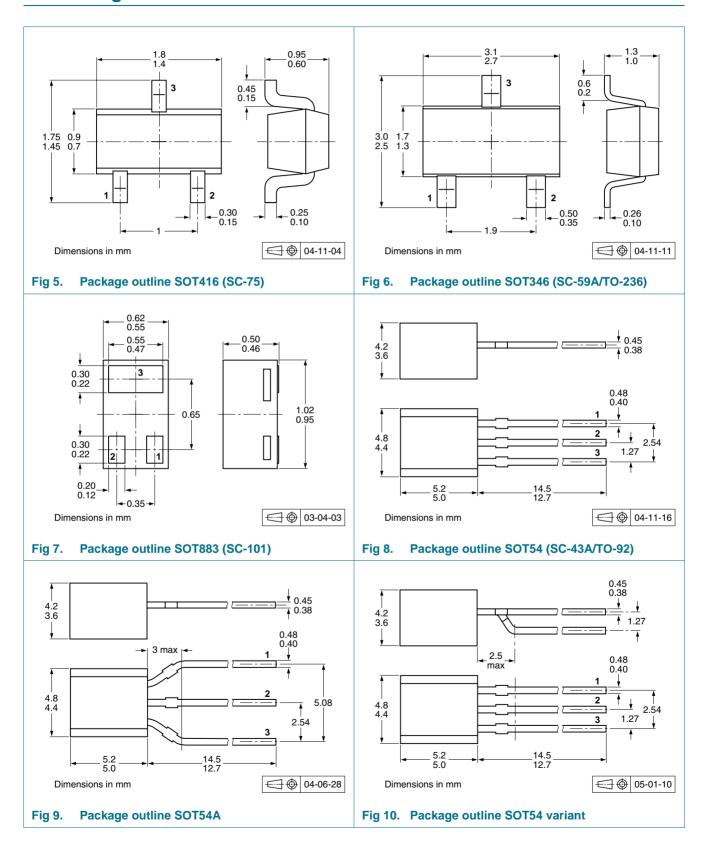
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

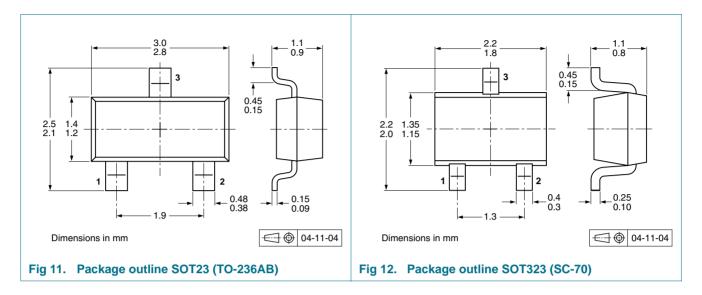
Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



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NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω



Packing information

Table 9. **Packing methods**

Product data sheet

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing (Packing quantity		
			3000	5000	10000	
PDTC123YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123YK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123YM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC123YS	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	-	-	-116	
		tape ammopack, wide pitch	-	-	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTC123YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC123YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

^[1] For further information and the availability of packing methods, see Section 12.

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NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

10. Revision history

Table 10. Revision history

Product data sheet

	•				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTC123Y_SER_4	20091116	Product data sheet	-	PDTC123Y_SER_3	
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 				
PDTC123Y_SER_3	20050324	Product data sheet	-	PDTC123YT_2	
PDTC123YT_2	20040510	Objective data sheet	-	PDTC123YT_1	
PDTC123YT_1	20040406	Objective data sheet	-	-	

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC123Y series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

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